

**AMENDMENTS TO THE CLAIMS**

1. (Currently Amended) A semiconductor device formed on a substrate,  
comprising:  
  
an interconnection line formed on said substrate and provided to structure a prescribed circuit; and  
  
a fuse incorporated into said interconnection line,  
  
said fuse and a connection portion of said interconnection line electrically connected to the fuse being formed of different metals, wherein  
  
an oxidation speed of the metal forming said fuse is faster than an oxidation speed of the metal forming the connection portion of said interconnection line.
2. (Cancelled).
3. (Original) The semiconductor device according to claim 1, wherein  
  
said fuse is formed of a copper metal, and  
  
the connection portion of said interconnection line is formed of an aluminum metal.
4. (Original) The semiconductor device according to claim 3, wherein  
  
said fuse is formed of the copper metal formed in a damascene process and planarized by a CMP (Chemical Mechanical Polishing) process.
5. (Currently Amended) ~~The semiconductor device according to claim 1~~  
semiconductor device formed on a substrate, comprising:

an interconnection line formed on said substrate and provided to structure a prescribed circuit; and

a fuse incorporated into said interconnection line,

said fuse and a connection portion of said interconnection line electrically connected to the fuse being formed of different metals, wherein

said interconnection line is formed as a multilayer interconnection line,

said fuse is provided at a same layer as one layer of the multilayer interconnection line,

and

an antireflection layer is provided closer to said substrate than a layer of said fuse is.

6. (Original) The semiconductor device according to claim 5, wherein

said antireflection layer includes a first antireflection layer extending in a direction of a length of said fuse, and a second antireflection layer extending in a direction traversing the first antireflection layer.

7. (Currently Amended) ~~The semiconductor device according to claim 1, 1A~~  
semiconductor device formed on a substrate, comprising:

an interconnection line formed on said substrate and provided to structure a prescribed circuit; and

a fuse incorporated into said interconnection line,

said fuse and a connection portion of said interconnection line electrically connected to the fuse being formed of different metals, wherein

said interconnection line is formed as a multilayer interconnection line,

said fuse is provided at a same layer as one layer of the multilayer interconnection line,  
and  
a reflection layer is provided closer to said substrate than a layer of said fuse is.

8. (Original) The semiconductor device according to claim 7, wherein  
said reflection layer includes a dummy metal line provided between said fuses in a planar  
view and a transparent resin film covering the dummy metal line, said transparent resin film  
forming a recessed and protruded surface having a portion overlying the dummy metal line and  
projecting closer to said fuse than a portion between the dummy metal lines.

9. (Original) The semiconductor device according to claim 1, wherein  
said fuse is formed from at least two portions different in width..

10. (Currently Amended) ~~A~~ The semiconductor device according to claim 1,  
wherein formed on a substrate, comprising:  
~~an interconnection line formed on said substrate and provided to structure a prescribed~~  
~~circuit; and~~  
~~a fuse incorporated into said interconnection line;~~  
said fuse ~~having~~ has a width gradually reduced from an end toward an intermediate  
portion of said fuse.

11. (Original) The semiconductor device according to claim 10, wherein  
said fuse has at least three different widths from the end toward the intermediate portion.